

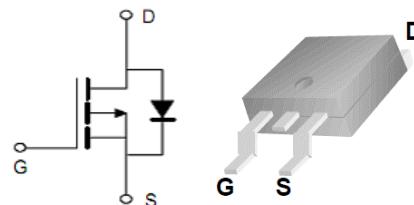
**Features**

- Improved dv/dt Capability, High Ruggedness
- Maximum Junction Temperature Range (150°C)

$V_{(BR)DSS}$	-60	V
$I_D$	-25	A
$R_{DS(ON)} @ V_{GS} = -10V$	35	mΩ
$R_{DS(ON)} @ V_{GS} = -4.5V$	45	mΩ

**Applications**

- DC Fan
- Brushless motor
- Optimized for Power Management Applications for Portable Products, such as H-bridge, Inverters Car Charger and Others


**TO-252**
**Order Information**

Product	Package	Marking	Reel Size	Reel	Carton
IRFR9024NTRPBF-CN	TO-252	CD35RP06M	13inch	2500PCS	50000PCS

**Absolute Maximum Ratings**

Symbol	Parameter	Value	Unit	
<b>Common Ratings (TC=25°C Unless Otherwise Noted)</b>				
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	-60	V	
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V	
$T_J$	Maximum Junction Temperature	150	°C	
$T_{STG}$	Storage Temperature Range	-50 to 150	°C	
$I_S$	Diode Continuous Forward Current	$T_c = 25^\circ C$	-25	A

**Mounted on Large Heat Sink**

$E_{AS}$	Single Pulse Avalanche Energy (Note1)	34	mJ	
$I_{DM}$	Pulse Drain Current Tested (Silicon Limit) (Note2)	$T_c = 25^\circ C$	-100	A
$I_D$	Continuous Drain current	$T_c = 25^\circ C$	-25	A
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	58	W
$R_{\theta JC}$	Thermal Resistance Junction-to-Case (Note3)	2.16	°C/W	

**P-Channel Electrical Characteristics**

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
<b>Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)</b>						
$V_{(BR)DSS}$	Drain- Source Breakdown Voltage	$VGS=0V$ $ID=-250\mu A$	-60	--	--	V
$I_{DSS}$	Zero Gate Voltage Drain current	$VDS=-60V, VGS=0V$	--	--	1	$\mu A$
$I_{GSS}$	Gate-Body Leakage Current	$VGS=\pm 20V, VDS=0V$	--	--	$\pm 100$	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$VDS=VGS, ID=-250\mu A$	-1	-2	-2.5	V
$R_{DS(ON)}$	Drain-Source On-State Resistance (Note4)	$VGS=-10V, ID=-15A$	--	35	42	$m\Omega$
		$VGS=-4.5V, ID=-10A$	--	45	53	$m\Omega$

**Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated) (Note5)**

$C_{iss}$	Input Capacitance	VDS= -30V, $VGS=0V,$ $F=1MHz$	--	946	--	pF
$C_{oss}$	Output Capacitance		--	188	--	pF
$C_{rss}$	Reverse Transfer Capacitance		--	8.8	--	pF
$Q_g$	Total Gate Charge	VDS= -30V, $ID= -7A,$ $VGS= -10V$	--	12.8	--	nC
$Q_{gs}$	Gate-Source Charge		--	3.2	--	nC
$Q_{gd}$	Gate-Drain Charge		--	1.5	--	nC

**Switching Characteristics (Note5)**

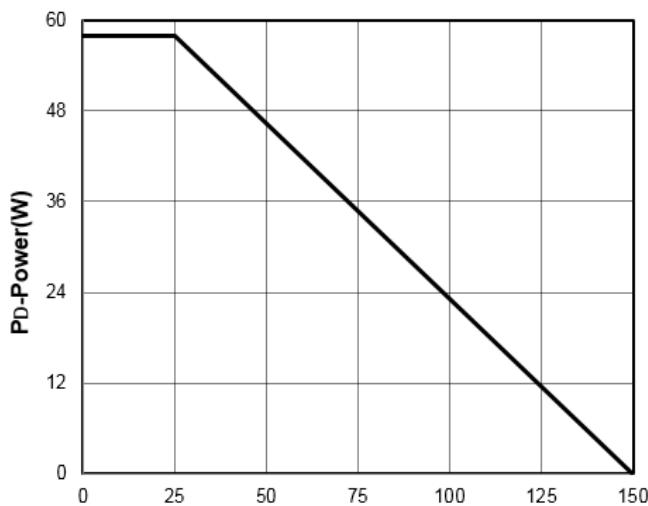
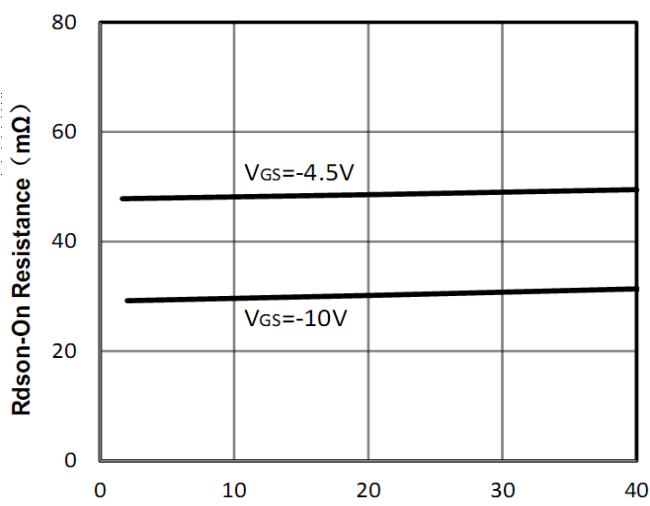
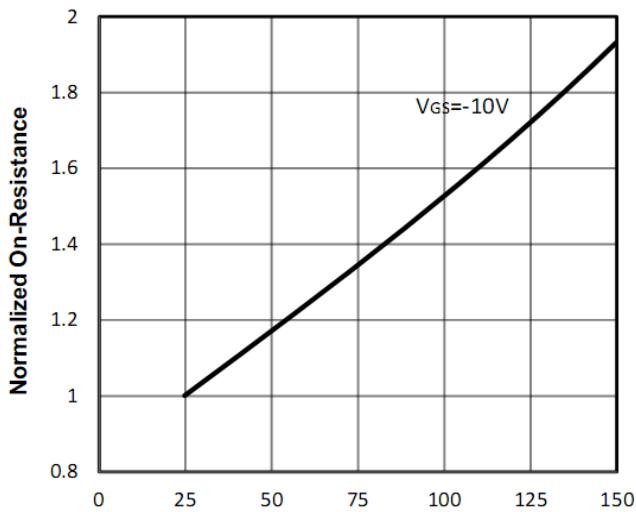
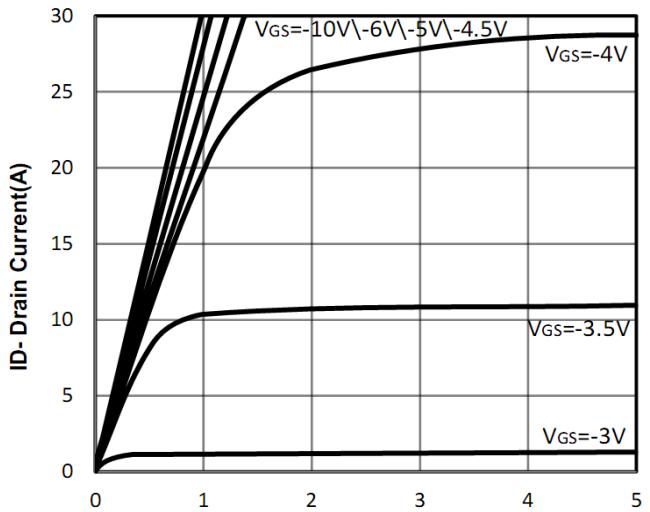
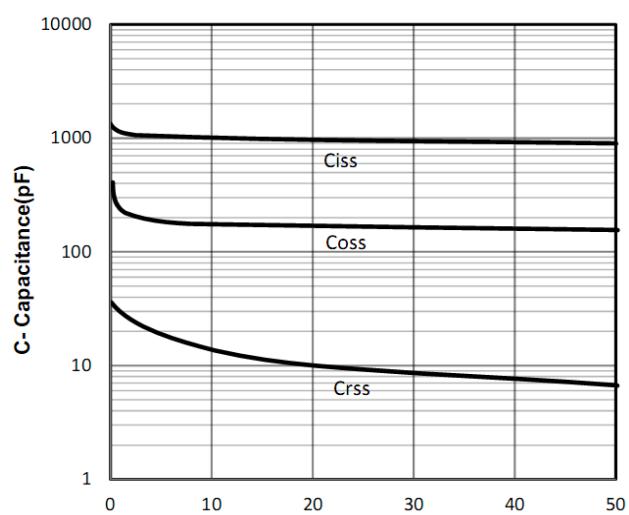
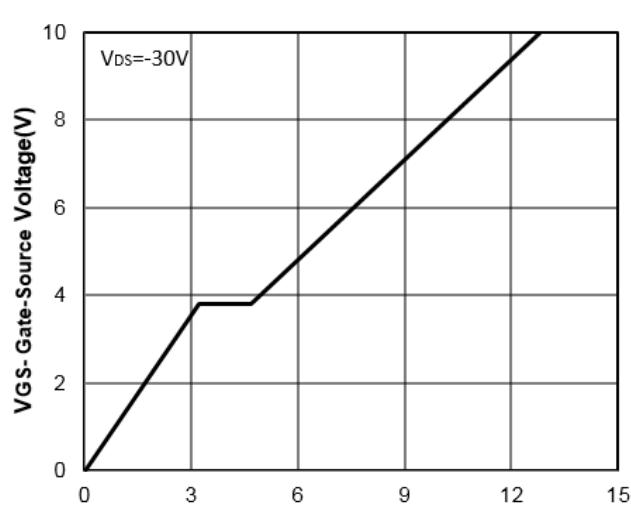
$t_{d(on)}$	Turn-on Delay Time	VDD=- 30V, $ID=-4A,$ $VGS=-10V,$ $RG=3\Omega$	--	5.3	--	nS
$t_r$	Turn-on Rise Time		--	1.6	--	nS
$t_{d(off)}$	Turn-off Delay Time		--	20	--	nS
$t_f$	Turn-off Fall Time		--	3.9	--	nS

**Source- Drain Diode Characteristics@ TJ = 25°C (unless otherwise stated)**

$V_{SD}$	Forward on voltage	$IS=-25A, VGS=0V$	--	--	-1.2	V
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Note:

1. Limited by  $TJmax$ , starting  $TJ = 25^\circ C$ ,  $RG = 4.5\Omega$ ,  $VD = -20V$ ,  $VGS = -10V$ . Part not recommended for use above this value.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
4. Pulse Test: pulse width  $\leq 300$  us, duty cycle  $\leq 2\%$ .
5. Guaranteed by design, not subject to production testing.

**Typical Characteristics**

**Figure1:**  $T_j$  -Junction Temperature (°C)

**Figure2:**  $-I_d$  -Drain Current (A)

**Figure3:**  $-T_j$  Junction Temperature (°C)

**Figure4:**  $-V_{DS}$  –Drain Source Voltage (V)

**Figure5:**  $-V_{DS}$  –Drain Source Voltage (V)

**Figure6:**  $Q_g$  -Gate Charge (nC)

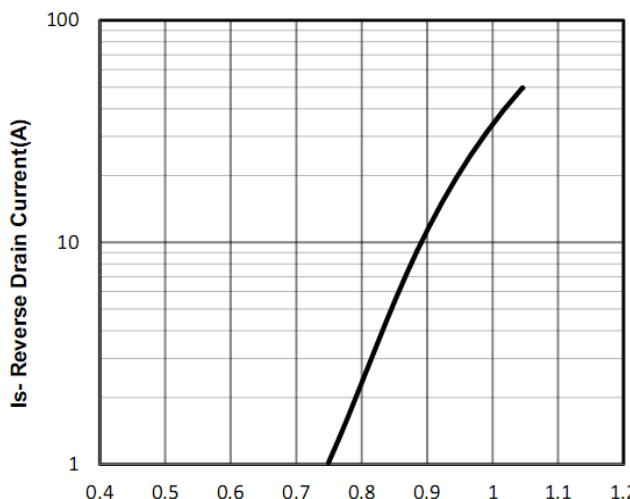


Figure7: - $V_{sd}$  –Source Drain Voltage (V)

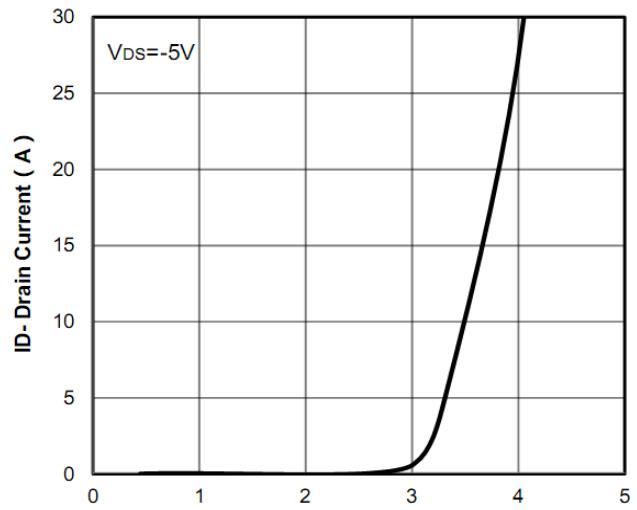


Figure8: - $V_{gs}$  –Gate Source Voltage (V)

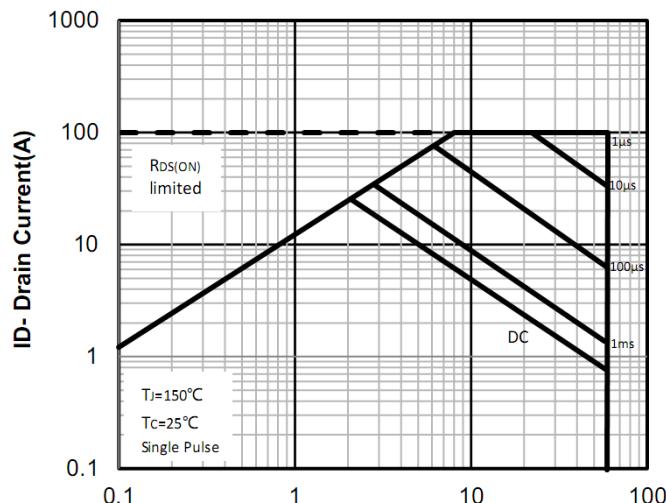


Figure9: - $V_{ds}$  –Drain Source Voltage (V)

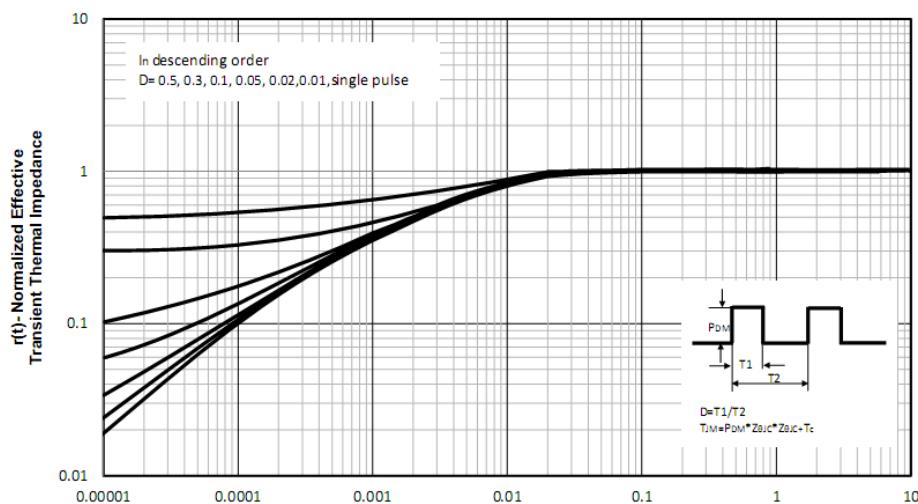


Figure10: Square Wave Pulse Duration (sec)

Test Circuit and Waveform (P-Channel):

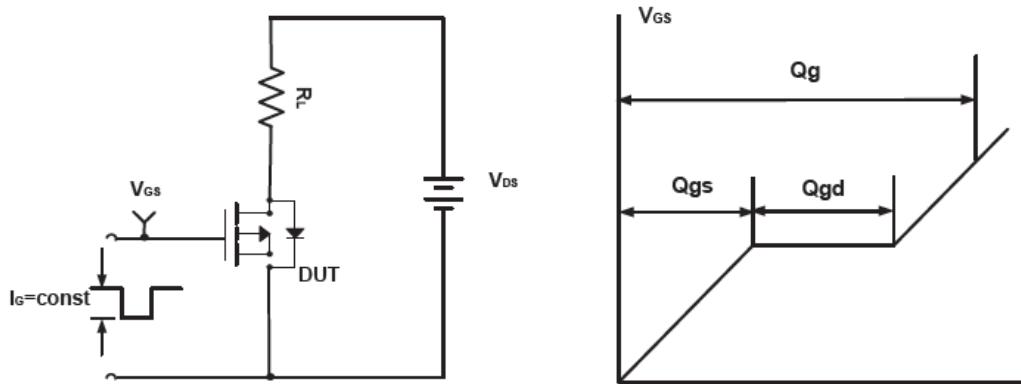


Figure A Gate Charge Test Circuit & Waveforms

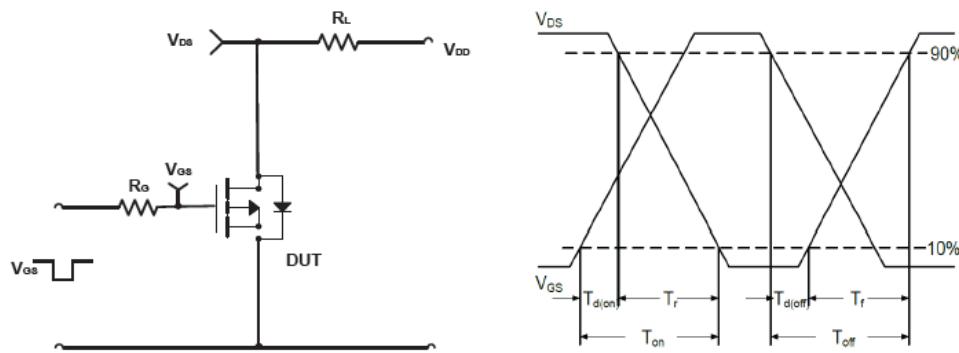


Figure B Switching Test Circuit & Waveforms

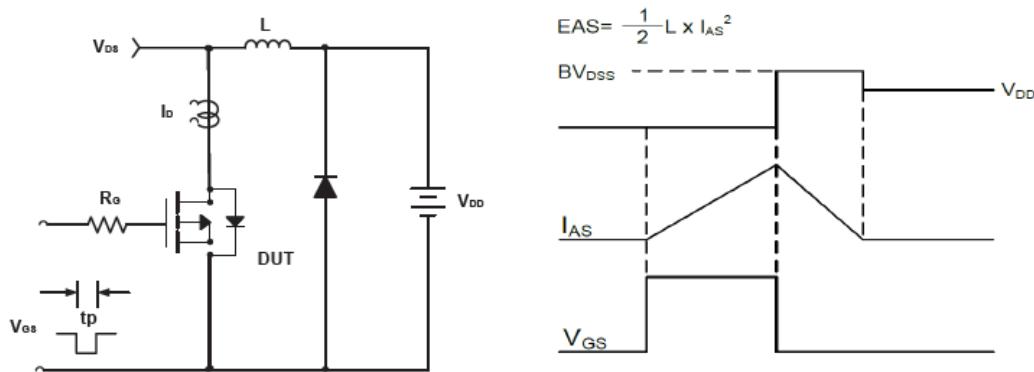
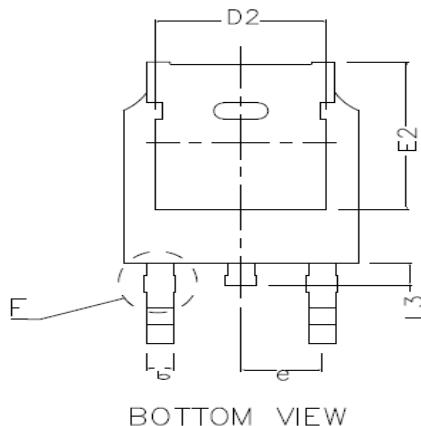
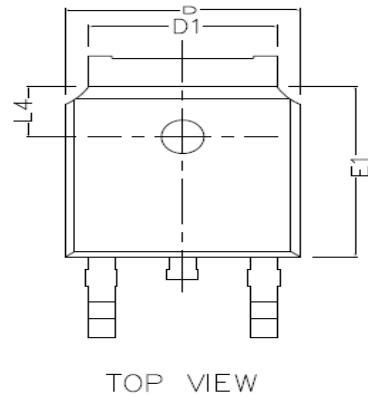


Figure C Unclamped Inductive Switching Circuit & Waveforms

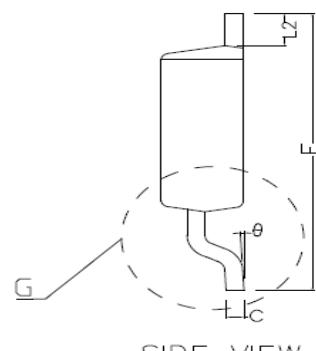
**TO-252 Package Outline Dimensions (Units: mm)**



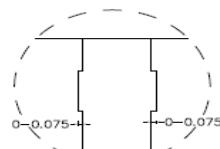
BOTTOM VIEW



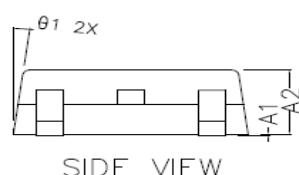
TOP VIEW



SIDE VIEW



DETAIL F



DETAIL G

COMMON DIMENSIONS (UNITS OF MEASURE IS mm)			
	MIN	NORMAL	MAX
A1	0.000	0.100	0.150
A2	2.200	2.300	2.400
A3	1.020	1.070	1.120
b	0.710	0.760	0.810
c	0.460	0.508	0.550
D	6.500	6.600	6.700
D1	5.330REF		
D2	4.830REF		
E	9.900	10.100	10.300
E1	6.000	6.100	6.200
E2	5.600REF		
e	2.286TYPE		
L	1.400	1.550	1.700
L2	1.10REF		
L3	0.80REF		
L4	1.80REF		
θ	0~8°		
θ1	7° TYPE		
θ2	10° TYPE		
θ3	10° TYPE		

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